

SFF150

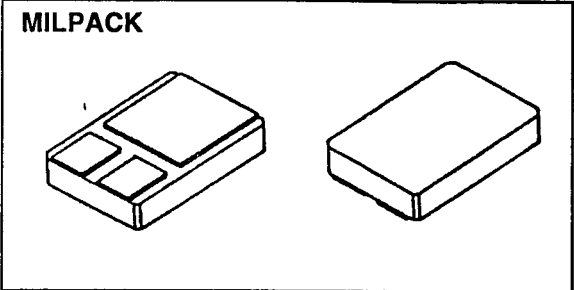
14849 Firestone Boulevard · La Mirada, CA 90638
 Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

Designer's Data Sheet

FEATURES:

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed power surface mount package
- TX, TXV and Space Level screening available
- Replaces: IRF150 Types

**30 AMP
 100 VOLTS
 0.055 Ω
 N-CHANNEL
 POWER MOSFET**



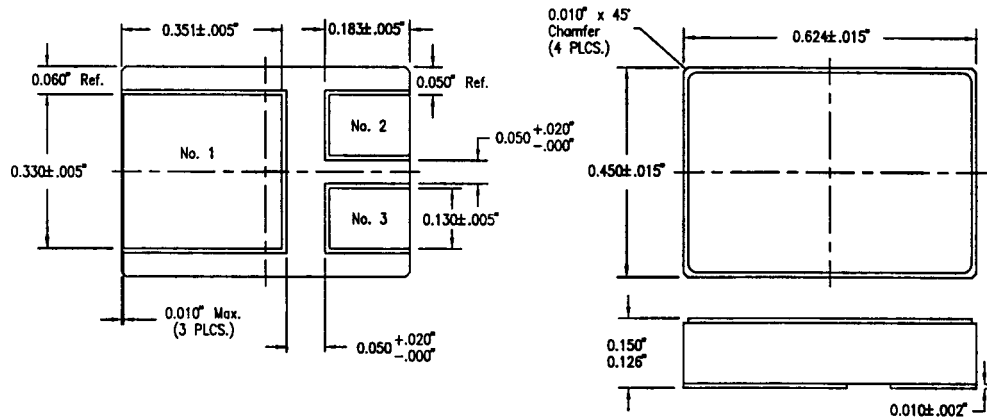
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	100	Volts
Gate to Source Voltage	V _{GS}	± 20	Volts
Continuous Drain Current	I _D	30	Amps
Operating and Storage Temperature	Top & Tstg	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1	°C/W
Total Device Dissipation @ TC=25°C	P _D	125	Watts
Total Device Dissipation @ TC=55°C		95	

PACKAGE OUTLINE: MILPACK

PIN OUT:

- PIN 1: DRAIN
 PIN 2: SOURCE
 PIN 3: GATE



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00043 C

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SFF150

PRELIMINARY

**SOLID STATE DEVICES, INC**14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**ELECTRICAL CHARACTERISTICS @ T_J=25°C (Unless Otherwise Specified)**

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250μA)		BV _{DSS}	100	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=20 A)		R _{DS(on)}	---	---	0.055	Ω
On State Drain Current (VDS > ID(on) X R _{DS(on)} Max, VGS=10 V)		ID(on)	30	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250μA)		VGS(th)	2	---	4	V
Forward Transconductance (VDS > ID(on) X R _{DS(on)} Max, IDS=20 A)		g _{fs}	9	11	---	S(Ω)
Zero Gate Voltage Drain Current (VDS=max rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		I _{DSS}	---	---	250 1000	μA
Gate to Source Leakage Forward	At rated VGS	I _{GSS}	---	---	100	nA
Gate to Source Leakage Reverse			---	---	100	
Total Gate Charge	VGS=10 Volts 80% rated VDS Rated ID	Q _g	---	63	120	nC
Gate to Source Charge		Q _{gs}	---	27	---	
Gate to Drain Charge		Q _{gd}	---	36	---	
Turn on Delay Time	VDD= 24 V ID= 20 A RG= 6.2 Ω	td(on)	---	---	35	nsec
Rise Time		tr	---	---	100	
Turn Off Delay Time		td(off)	---	---	125	
Fall Time		tf	---	---	100	
Diode Forward Voltage (IS= 40 A, VGS=0 V, T _J =25°C)		VSD	---	---	2.5	V
Diode Reverse Recovery Time	T _J =25°C IF=40 A di/dt=100 A/μsec	t _{rr}	---	600	---	nsec
Reverse Recovery Charge		Q _{RR}	---	3.3	---	μC
Input Capacitance	VGS=0 Volts VDS=25 Volts f= 1 MHz	C _{iss}	---	2000	3000	pF
Output Capacitance		C _{oss}	---	1000	1500	
Reverse Transfer Capacitance		C _{rss}	---	350	500	

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.